

Silicon PNP Power Transistors

2SA1117

DESCRIPTION

- With TO-3 package
- High power dissipations

APPLICATIONS

- For power switching amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

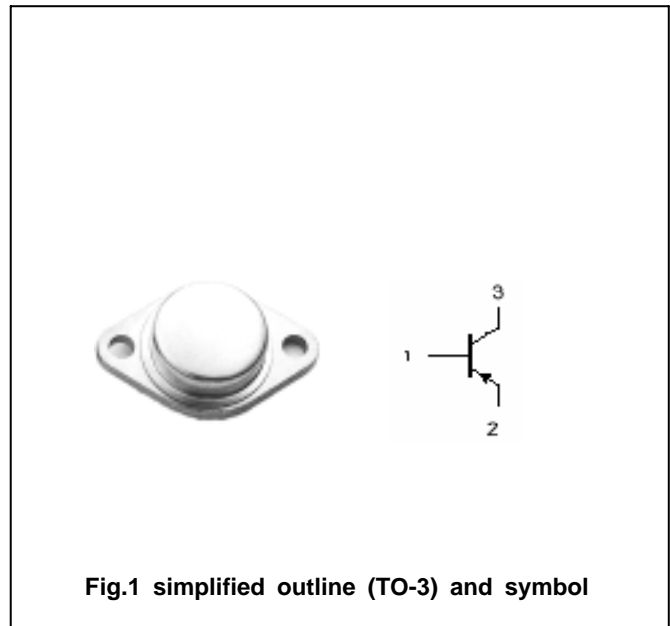


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-200	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-17	A
I_B	Base current		-5	A
P_C	Collector power dissipation	$T_C=25$	200	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.0	V
I _{CB0}	Collector cut-off current	V _{CB} =-200V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-8A ; V _{CE} =-4V	20			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-12V		20		MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)